CMOS Quad 3-State R/S Latches

High-Voltage Types (20-Volt Rating)
Quad NOR R/S Latch – CD4043B
Quad NAND R/S Latch – CD4044B

The RCA-CD4043B types are quad cross-coupled 3-state CMOS NOR latches and the CD4044B types are quad cross-coupled 3-state CMOS NAND latches. Each latch has a separate Q output and individual SET and RESET inputs. The Q outputs are controlled by a common ENABLE input. A logic "1" or high on the ENABLE input connects the latch states to the Q outputs. A logic "0" or low on the ENABLE input disconnects the latch states from the Q outputs, resulting in an open circuit condition on the Q outputs. The open circuit feature allows common bussing of the outputs.

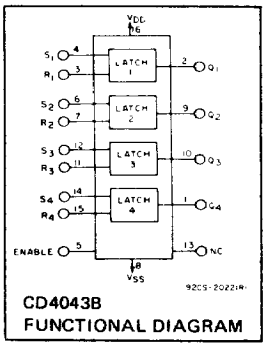
The CD4043B and CD4044B types are supplied in 16-lead hermetic dual-in-line ceramic packages (D and F suffixes), 16-lead dual-in-line plastic packages (E suffix), 16-lead ceramic flat packages (K suffix), and in chip form (H suffix).

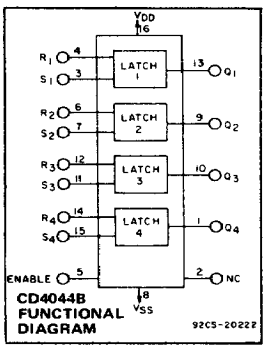
Features:

- 3-state outputs with common output ENABLE
- Separate SET and RESET inputs for each latch
- NOR and NAND configurations
- 5-V, 10-V, and 15-V parametric ratings
- Standardized symmetrical output characteristics
- 100% tested for quiescent current at 20 V
- Maximum input current of 1 μA at 18 V over full package temperature range; 100 nA at 18 V and 25°C
- Noise margin (over full package temperature range): 1 V at V_{DD} = 5 V, 2 V at V_{DD} = 10 V, 2.5 V at V_{DD} = 15 V
- Meets all requirements of JEDEC Tentative Standard No. 13A, "Standard Specifications for Description of 'B' Series CMOS Devices"

Applications:

- Holding register in multi-register system
- Four bits of independent storage with output ENABLE
- Strobed register
- General digital logic
- CD4043B for positive logic systems
- CD4044B for negative logic systems





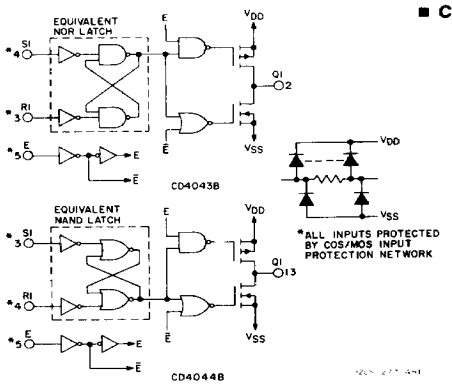
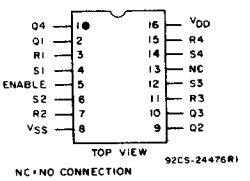
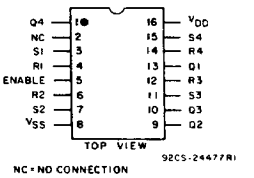


Fig. 1 – Logic diagrams.





TERMINAL ASSIGNMENTS

S	R	E	Q
X	X	0	OC*
0	0	1	NC+
1	0	1	1
0	1	1	0
1	1	1	Δ

*OPEN CIRCUIT
+NO CHANGE
Δ DOMINATED BY S=1 INPUT
92CS-20211
CD4043B

S	R	E	Q
X	X	0	OC*
1	1	1	NC+
0	1	1	1
1	0	1	0
0	0	1	ΔΔ

*OPEN CIRCUIT
+NO CHANGE
ΔΔ DOMINATED BY R=0 INPUT
92CS-20212
CD4044B

MAXIMUM RATINGS, *Absolute-Maximum Values:*

DC SUPPLY-VOLTAGE RANGE, (V_{DD})
(Voltages referenced to V_{SS} Terminal) ..... -0.5 to +20 V
INPUT VOLTAGE RANGE, ALL INPUTS ..... -0.5 to V_{DD} +0.5 V
DC INPUT CURRENT, ANY ONE INPUT ..... ±10 mA
POWER DISSIPATION PER PACKAGE (P_D):
For T_A = -40 to +60°C (PACKAGE TYPE E) ..... 500 mW
For T_A = +60 to +85°C (PACKAGE TYPE E) ..... Derate Linearly at 12 mW/°C to 200 mW
For T_A = -55 to +100°C (PACKAGE TYPES D, F, K) ..... 500 mW
For T_A = +100 to +125°C (PACKAGE TYPES D, F, K) ..... Derate Linearly at 12 mW/°C to 200 mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR:
For T_A = FULL PACKAGE-TEMPERATURE RANGE (All Package Types) ..... 100 mW
OPERATING-TEMPERATURE RANGE (T_A):
PACKAGE TYPES D, F, K, H ..... -55 to +125°C
PACKAGE TYPE E ..... -40 to +85°C
STORAGE TEMPERATURE RANGE (T_{stg}) ..... -65 to +150°C
LEAD TEMPERATURE (DURING SOLDERING):
At distance 1/16 ± 1/32 inch (1.59 ± 0.79 mm) from case for 10 s max. ..... +265°C

TRUTH TABLES

CD4044B

Recommended Operating Conditions T_A=25°C
For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges.

Characteristic	V_{DD} (V)	Min.	Max.	Units
Supply-Voltage Range (T_A = Full Package Temperature Range)	–	3	18	V
SET or RESET Pulse Width, t_W	5	160	–	ns
	10	80	–	
	15	40	–	

STATIC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C) Values at -55, +25, +125 Apply to D, F, K, H Packages Values at −40, +25, +85 Apply to E Package							UNITS
								+25			
	V_O (V)	V_{IN} (V)	V_{DD} (V)	−55	−40	+85	+125	Min.	Typ.	Max.	
Quiescent Device Current, I_{DD} Max.	–	0,5	5	1	1	30	30	–	0.02	1	μA
	–	0,10	10	2	2	60	60	–	0.02	2	
	–	0,15	15	4	4	120	120	–	0.02	4	
	–	0,20	20	20	20	600	600	–	0.04	20	
Output Low (Sink) Current I_{OL} Min.	0.4	0,5	5	0.64	0.61	0.42	0.36	0.51	1	–	mA
	0.5	0,10	10	1.6	1.5	1.1	0.9	1.3	2.6	–	
	1.5	0,15	15	4.2	4	2.8	2.4	3 4	6.8	–	
Output High (Source) Current, I_{OH} Min.	4.6	0,5	5	−0.64	−0.61	−0.42	−0.36	−0.51	−1	–	
	2.5	0,5	5	−2	−1.8	−1.3	−1.15	−1.6	−3.2	–	
	9.5	0,10	10	−1.6	−1.5	−1.1	−0.9	−1.3	−2.6	–	
	13.5	0,15	15	−4.2	−4	−2.8	−2.4	−3.4	−6.8	–	
Output Voltage: Low-Level, V_{OL} Max.	–	0,5	5	0.05				–	0	0.05	V
	–	0,10	10	0.05				–	0	0.05	
	–	0,15	15	0.05				–	0	0.05	
Output Voltage: High-Level, V_{OH} Min.	–	0,5	5	4.95				4.95	5	–	
	–	0,10	10	9.95				9.95	10	–	
	–	0,15	15	14.95				14.95	15	–	
Input Low Voltage, V_{IL} Max.	0.5, 4.5	–	5	1.5				—	—	1.5	V
	1, 9	–	10	3				–	—	3	
	1.5,13.5	–	15	4				–	—	4	
Input High Voltage, V_{IH} Min.	0.5, 4.5	–	5	3.5				3.5	—	—	
	1, 9	–	10	7				7	—	—	
	1.5, 3.5	–	15	11				11	—	—	
Input Current I_{IN} Max.	–	0,18	18	±0.1	±0.1	±1	±1	–	$\pm 10^{-5}$	±0.1	μA
3-State Output Leakage Current I_{OUT} Max.	0,18	0,18	18	±0.4	±0.4	±12	±12	—	$\pm 10^{-4}$	±0.4	μA

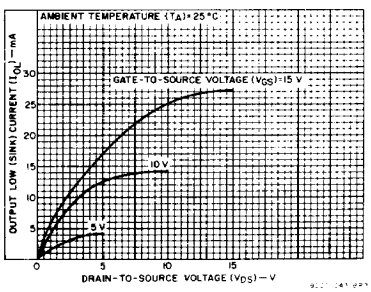


Fig. 2 – Typical output low (sink) current characteristics.

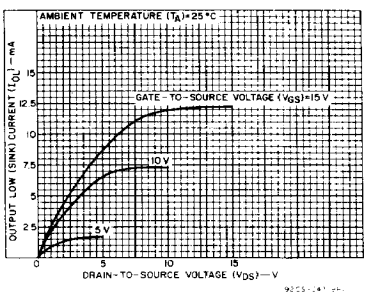


Fig. 3 – Minimum output low (sink) current characteristics.

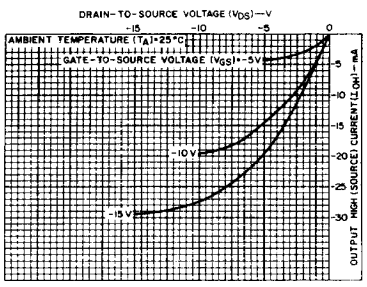


Fig. 4 – Typical output high (source) current characteristics.

DYNAMIC ELECTRICAL CHARACTERISTICS *at T_A = 25° C; Input t_r, t_f = 20 ns, C_L = 50 pF, R_L = 200 KΩ*

CHARACTERISTIC	V_{DD} (V)	LIMITS ALL TYPES TYP.	LIMITS ALL TYPES MAX.	UNITS
Propagation Delay Time: t_{PHL}, t_{PLH} SET or RESET to Q	5	150	300	ns
	10	70	140	
	15	50	100	
3-State Propagation Delay Time: ENABLE to Q t_{PHZ}, t_{PZH}	5	115	230	ns
	10	55	110	
	15	40	80	
t_{PLZ}, t_{PZL}	5	90	180	ns
	10	50	100	
	15	35	70	
Transition Time: t_{THL}, t_{TLH}	5	100	200	ns
	10	50	100	
	15	40	80	
Minimum SET or RESET Pulse Width, t_W	5	80	160	ns
	10	40	80	
	15	20	40	
Input Capacitance, (Any Input) C_{IN}	–	5	7.5	pF

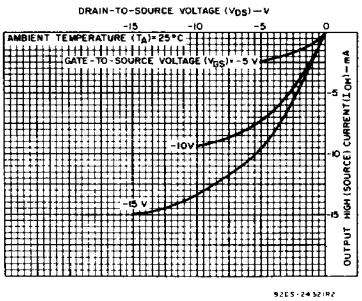


Fig. 5 – Minimum output high (source) current characteristics.

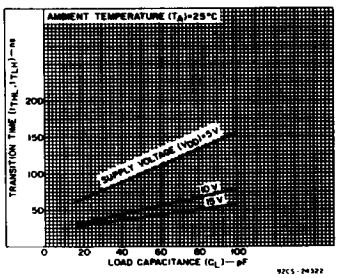


Fig. 6 – Typical transition time vs. load capacitance.

TEST CIRCUITS

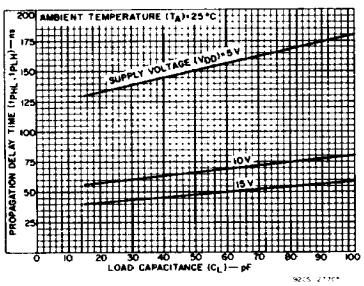


Fig. 7 – Typical propagation delay time vs. load capacitance—SET, RESET to Q, Q̄.

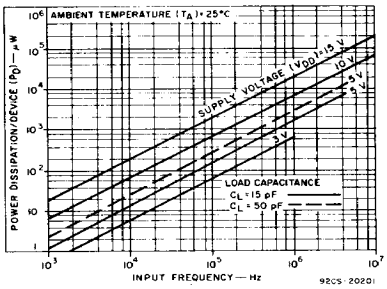


Fig. 8 – Typical power dissipation vs. frequency.

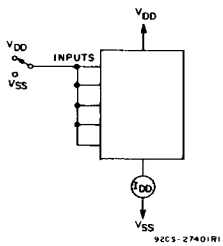


Fig. 9 – Quiescent device current.

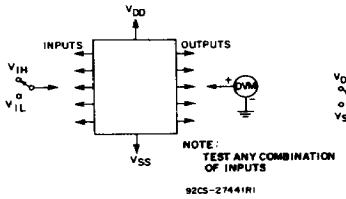


Fig. 10 – Input voltage.

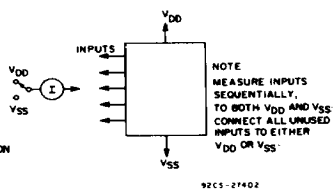


Fig. 11 – Input current.

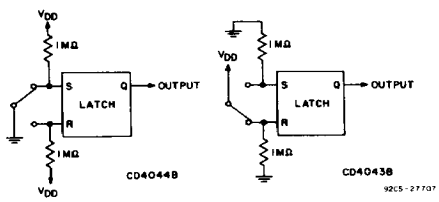


Fig. 12 – Switch bounce eliminator.

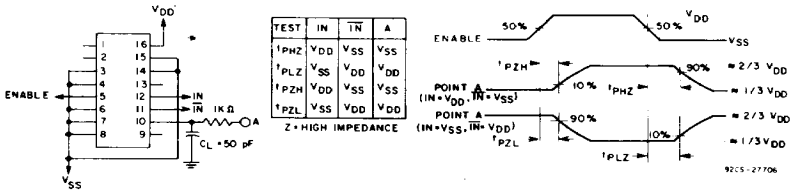
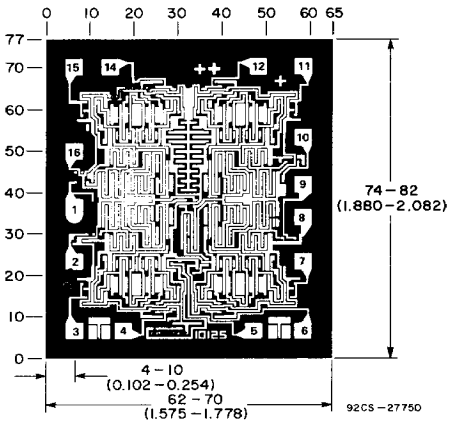
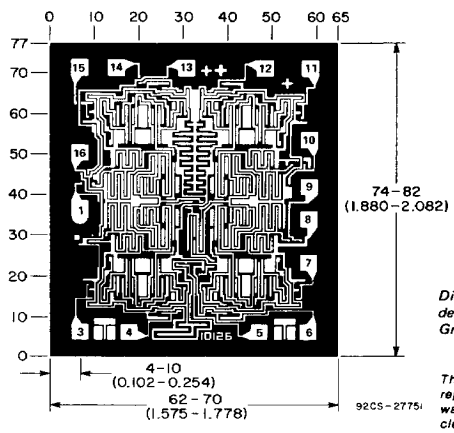


Fig. 13 – ENABLE propagation delay time test circuit and waveforms.

CHIP PHOTOGRAPHS DIMENSIONS AND PAD LAYOUTS



CD4043BH



CD4044BH

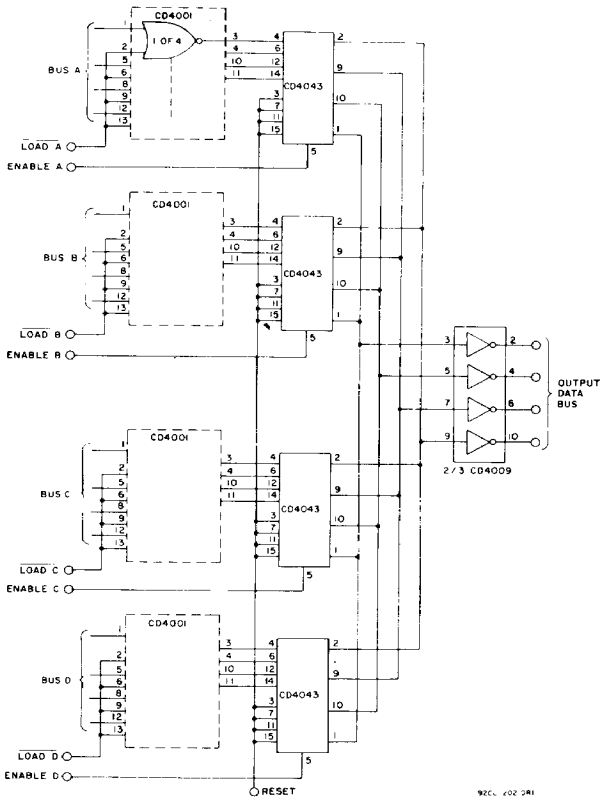


Fig. 14 – Multiple bus storage.

Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch).

The photographs and dimensions of each CMOS chip represent a chip when it is part of the wafer. When the wafer is separated into individual chips, the angle of cleavage may vary with respect to the chip face for different chips. The actual dimensions of the isolated chip, therefore, may differ slightly from the nominal dimensions shown. The user should consider a tolerance of −3 mils to +16 mils applicable to the nominal dimensions shown.